Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S42	2	"20020126073"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/09 11:16
S43	2	"20020093472"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/09 11:18
S44	2	"20020084840"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/09 11:19
S45	7830	(tft (thin adj film adj transistor)) same electrodes same (contact adj3 hole)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/09 11:20
S46	3300	(tft (thin adj film adj transistor)) same (electrodes near4 layer$3) same (contact adj3 hole)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/09 11:20
S47	8	(tft (thin adj film adj transistor)) same (electrodes with layer$3) same ((contact adj3 hole) near4 (insulating adj2 layer) near3 step$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/09 11:21
S48	24	("4704002").URPN.	USPAT	OR	ON	2005/11/09 11:47
S49	194	((contact near hole) same (etch$3 near3 rate)) and (tft (thin adj film adj transistor))	USPAT	OR	ON	2005/11/09 13:31
S50	4	("5227012" | "6284558" | "6366331" | "6475836").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/11/09 12:09
S51	27	(((contact near hole) near4 step) same (etch$3 near3 rate)) and (tft (thin adj film adj transistor))	USPAT	OR	ON	2005/11/09 13:32
S52	9	("4495220" | "4814041" | "5258645" | "5371398" | "5475238" | "5583347" | "5619045" | "5620905" | "5719065").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/11/09 13:38
S53	6	("5130772" | "5296729" | "5440168" | "5468986" | "5616933" | "5917225").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/11/09 14:07

S54	6	("5962916").URPN.	USPAT	OR	ON	2005/11/09 15:05
S55	2	"10170955"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/09 15:05